

2SB1361

Silicon PNP triple diffusion planar type

For high power amplification
Complementary to 2SD2052

■ Features

- Satisfactory forward current transfer ratio h_{FE} vs. collector current I_C characteristics
- Wide area of safe operation (ASO)
- High transition frequency f_T
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

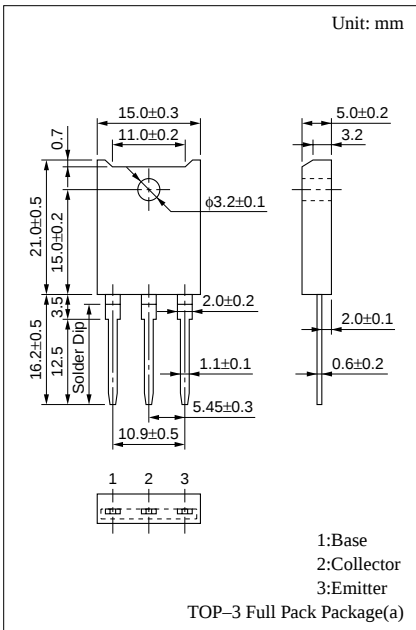
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-150	V
Collector to emitter voltage	V_{CEO}	-150	V
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-15	A
Collector current	I_C	-9	A
Collector power dissipation	P_C	$T_C=25^\circ\text{C}$	W
		$T_a=25^\circ\text{C}$	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

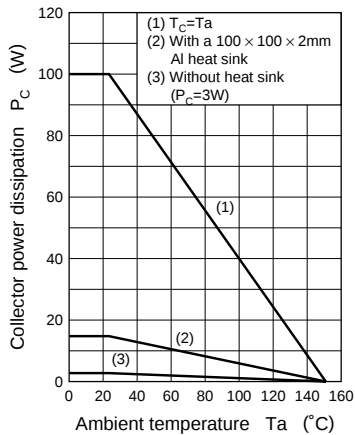
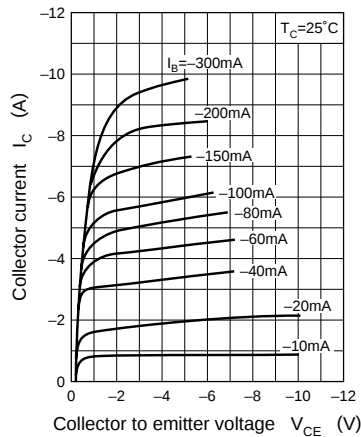
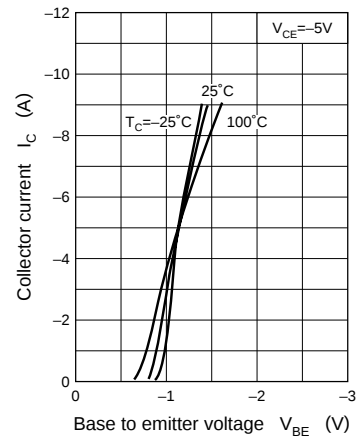
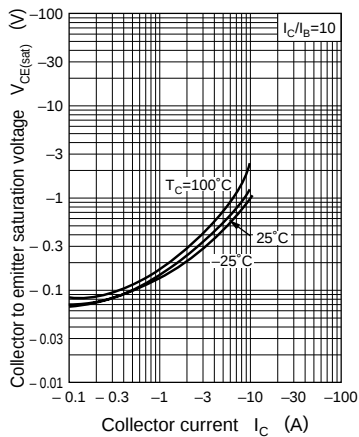
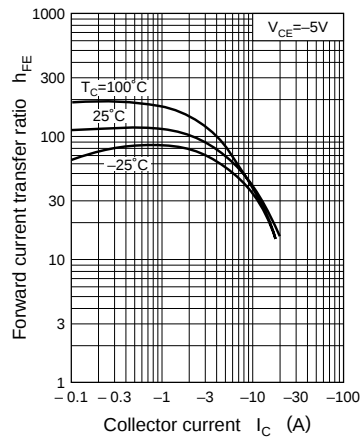
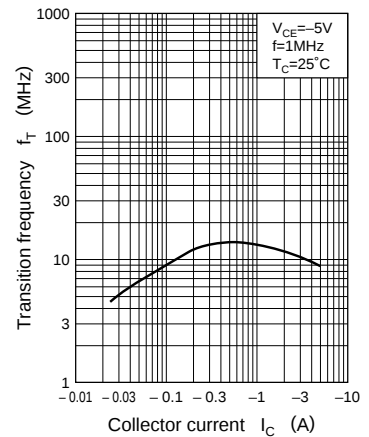
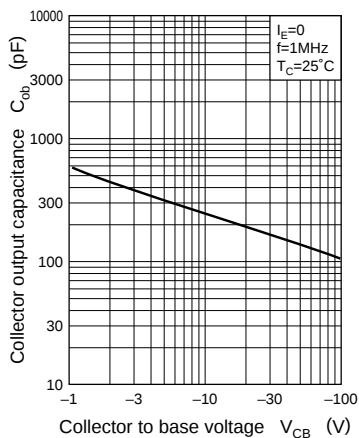
■ Electrical Characteristics ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -150\text{V}, I_E = 0$			-50	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$			-50	μA
Forward current transfer ratio	h_{FE1}	$V_{CE} = -5\text{V}, I_C = -20\text{mA}$	20			
	h_{FE2}^*	$V_{CE} = -5\text{V}, I_C = -1\text{A}$	60		200	
	h_{FE3}	$V_{CE} = -5\text{V}, I_C = -7\text{A}$	20			
Base to emitter voltage	V_{BE}	$V_{CE} = -5\text{V}, I_C = -7\text{A}$			-1.8	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -7\text{A}, I_B = -0.7\text{A}$			-2.0	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -0.5\text{A}, f = 1\text{MHz}$		15		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		270		pF

* h_{FE2} Rank classification

Rank	Q	S	P
h_{FE2}	60 to 120	80 to 160	100 to 200



$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(\text{sat})} - I_C$  $h_{FE} - I_C$  $f_T - I_C$  $C_{ob} - V_{CB}$ 

Area of safe operation (ASO)

